

Technical documentation



Support & training



CD74HC93, CD74HCT93 SCHS138D – NOVEMBER 1998 – REVISED MARCH 2022

CD74HC93, CD74HCT93 High-Speed CMOS Logic 4-Bit Binary Ripple Counter

1 Features

- Can be configured to divide by 2, 8, and 16
- Asynchronous reset
- Fanout (over temperature range)
 - Standard outputs: 10 LSTTL loads
 Bus driver outputs: 15 LSTTL loads
- Wide operating temperature range: 55°C to 125°C
- · Balances propagation delay and transition times
- Signigicant power reduction compared to LSTTL logic ICs
- · HC types
 - 2 V to 6 V operation
 - High noise immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}
- HCT types
 - 4.5 V to 5.5 V operation
 - Direct LSTTL input logic compatibility, V_{IL} = 0.8 V (max), V_{IH} = 2 V (min)
 - CMOS input compatibility, I_I ≤ 1 μ A at V_{OL}, V_{OH}

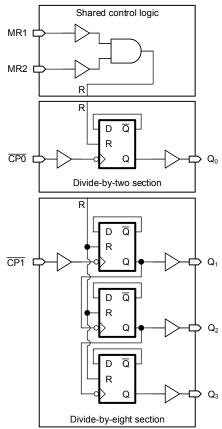
2 Description

The CD74HC93 and CD74HCT93 are high-speed silicon-gate CMOS devices and are pin-compatible with low power Schottky TTL (LSTTL). These 4-bit binary ripple counters consist of four flip-flops internally connected to provide a divide-by-two section and a divide-by-eight section. Each section has a separate clock input ($\overline{CP0}$ and $\overline{CP1}$) to initiate state changes of the counter on the HIGH to LOW clock transition. State changes of the Q_n outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used for clocks or strobes.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)					
CD74HC93M	SOIC (14)	8.65 mm × 3.90 mm					
CD74HC93E	PDIP (14)	19.31 mm × 6.35 mm					
CD74HCT93E	PDIP (14)	19.31 mm × 6.35 mm					

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.



Functional Block Diagram

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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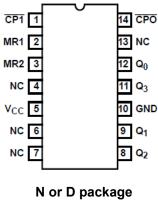
3 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	hanges from Revision C (September 2003) to Revision D (March 2022)	Page
•	Updated the numbering, formatting, tables, figures, and cross-references throughout the doucment to re	eflect
	modern data sheet standards	1



4 Pin Configuration and Functions



14-Pin PDIP or SOIC

Top View



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	7	V
I _{IK}	Input diode current ⁽²⁾	$(V_1 < -0.5 V \text{ or } V_1 > V_{CC} + 0.5 V)$		±20	mA
I _{ок}	Output diode current ⁽²⁾	$(V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V})$		±20	mA
I _O	Output source or sink current per output pin	$(V_{\rm O} > -0.5 \text{ V or } V_{\rm O} < V_{\rm CC} + 0.5 \text{ V})$		±25	mA
	Continuous current through V_{CC} c	or GND		±50	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 Recommended Operating Conditions

			MIN	NOM MAX	UNIT
V	Supply voltage	HC types	2	6	V
V _{CC}		HCT types	4.5	5.5	v
VI	Input voltage		0	V _{CC}	V
Vo	Output voltage		0	V _{CC}	V
		2 V		1000	
t _t	Input transition rise/fall time	4.5 V		500	ns
		6 V		400	
T _A	Operating free-air temperature		- 55	125	°C

5.3 Thermal Information

		D (SOIC)	N (PDIP)	
THERMAL METRI	c	14 PINS	14 PINS	UNIT
R _{θJA}	Junction-to-ambient thermal resistance ⁽¹⁾	86	80	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



5.4 Electrical Characteristics

	PARAMETER	TEST CONDITIONS ⁽¹⁾	V _{cc}	T	_A = 25°C	;	– 40°C t	o 85°C	– 55°C to 125°C		UNIT
			(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
НС ТҮР	PES										
			2	1.5			1.5		1.5		V
VIH	High level input voltage		4.5	3.15			3.15		3.15		V
			6	4.2			4.2		4.2		V
			2			0.5		0.5		0.5	V
V _{IL}	Low level input voltage		4.5			1.35		1.35		1.35	V
			6			1.8		1.8		1.8	V
		I _{OH} = – 20 μA	2	1.9			1.9		1.9		V
		I _{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
V _{OH}	High-level output voltage	I _{OH} = – 20 μA	6	5.9			5.9		5.9		V
		I _{OH} = – 4 mA	4.5	3.98			3.84		3.7		V
		I _{OH} = – 5.2 mA	6	5.48			5.34		5.2		V
		I _{OL} = 20 μA	2			0.1		0.1		0.1	V
		I _{OL} = 20 μA	4.5			0.1		10.1		0.1	V
V _{OL}	Low-level output voltage	I _{OL} = 20 μA	6			0.1		0.1		0.1	V
		I _{OL} = 4 mA	4.5			0.26		0.33		0.4	V
		I _{OL} = 5.2 mA	6			0.26		0.33		0.4	V
l _l	Input leakage current	V _{CC} or GND	6			±0.1		±1		±1	nA
I _{CC}	Supply current	V _{CC} or GND	6			8		80		160	μA
I _{CC}	Supply-current change	One input at 0.5 V or 2.4 V, Other inputs at 0 or V _{CC}	5.5		1.4	2.4		2.9			mA
C _i	Input capacitance		4.5 to 5.5		3	10		10			pF
НСТ ТҮ	(PES	-									
V _{IH}	High level input voltage		4.5 to 5.5	2			2		2		V
V _{IL}	Low level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
V	High level Output Voltage	I _{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
V _{OH}		I _{OH} = – 4 mA	4.5	3.98			3.84		3.7		V
V _{OL}	Low level output voltage	I _{OH} = 20 μA	4.5			0.1		0.1		0.1	V
VOL	Low level output voltage	I _{OH} = 4 mA	4.5			0.26		0.33		0.4	V
I	Input leakage current	V _{CC} or GND	5.5			±0.1		±1		±1	μA
I _{CC}	Supply current	V _{CC} or GND	5.5			8		80		160	μA
ΔI _{CC} ⁽²⁾	Additional supply current	CP0,CP1	4.5 to 5.5		100	216		270		294	μA
(3)	per input pin	CLR1, CLR2	4.5 to 5.5		100	144		180		196	μA

V_I = V_{IH} or V_{IL}, unless otherwise noted.
 For dual-supply systems theorietical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specifications is 1.8 mA.
 Inputs held at V_{CC} - 2.1.



5.5 Prerequisite for Switching Characteristics

	PARAMETER	V _{cc} (V)	25°C	:	– 40°C to	85°C	– 55°C to 125°C		
			MIN	MAX	MIN	MAX	MIN	MAX	UNIT
НС ТҮ	PES								
		2	6		5		4		MHz
f _{MAX}	Maximum clock frequency	4.5	30		24		20		MHz
		6	35		28		24		MHz
		2	80		100		120		ns
t _W	Clock pulse width CP0, CP1	4.5	16		20		24		ns
		6	14		17		20		ns
		2	80		100		120		ns
t _w	Reset pulse width	4.5	16		20		24		ns
		6	14		17		20		ns
		2	50		65		75		ns
t _{REM}	Reset removal time	4.5	10		13		15		ns
		6	9		11		13		ns
НСТ Т	YPES		1						
f _{MAX}	Maximum clock frequency	4.5	30		24		20		MHz
t _W	Clock pulse width CP0, CP1	4.5	16		20		24		ns
t _W	Reset pulse width	4.5	16		20		24		ns
t _{REM}	Reset removal time	4.5	10		13		15		ns

5.6 Switching Characteristics

Input t_r , t_f = 6ns. C_L = 50pF unless otherwise noted

	PARAMETER	V _{cc} (V)		25°C		– 40°C to 85°C	– 55°C to 125°C	UNIT
	PARAMETER		MIN	TYP	MAX	MIN MAX	MIN MAX	UNIT
НС ТҮРЕ	S							
		2			125	155	190	ns
t _{PLH} , t _{PHL}	CP0 to Q0	4.5		10 ⁽¹⁾	25	31	38	ns
		6			21	26	32	ns
		2			135	170	205	ns
t _{PLH} , t _{PHL}	CP1 to Q1	4.5			27	34	41	ns
		6			23	29	35	ns
		2			185	230	280	ns
t _{PLH} , t _{PHL}	CP1 to Q2	4.5			37	46	56	ns
		6			31	39	48	ns
		2			245	305	370	ns
t _{PLH} , t _{PHL}	CP1 to Q3	4.5		21 ⁽¹⁾	49	61	74	ns
		6			42	52	63	ns
		2			155	195	235	ns
t _{PLH} , t _{PHL}	MR1, MR2 to Qn	4.5		13 ⁽¹⁾	31	39	47	ns
		6			26	33	40	ns
		2			75	95	110	ns
t _{TLH} , t _{THL}	Output transition time	4.5			15	19	22	ns
		6			13	16	19	ns
C _{IN}	Input capacitance				10	10	10	pF



5.6 Switching Characteristics (continued)

Input t_r , t_f = 6ns. C_L = 50pF unless otherwise noted

	PARAMETER	V _{cc} (V)	25°C		– 40°C to 85°C		– 55°C to 125°C		UNIT	
	FARAIVIETER		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
C _{PD}	Power dissipation capacitance			25			10		19	pF
НСТ ТҮР	ES									
t _{PLH} , t _{PHL}	CP0 to Q0	4.5		14 ⁽¹⁾	34		43		51	ns
t _{PLH} , t _{PHL}	CP1 to Q1	4.5			34		43		51	ns
t _{PLH} , t _{PHL}	CP1 to Q2	4.5			46		58		69	ns
t _{PLH} , t _{PHL}	CP1 to Q3	4.5		24 ⁽¹⁾	58		73		87	ns
t _{PLH} , t _{PHL}	MR1, MR2 to Qn	4.5		13 ⁽¹⁾	33		41		50	ns
t _{TLH} , t _{THL}	Output Transition time	4.5			15		19		22	ns
C _{IN}	Input Capacitance				10		10		10	pF
C _{PD}	Power dissipation capacitance			25						pF

(1) $C_L = 15 p F. V_{CC} = 5.$

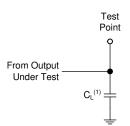


6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 6 ns.

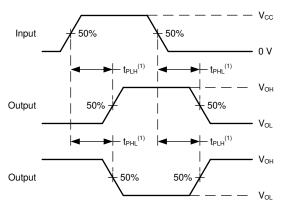
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.

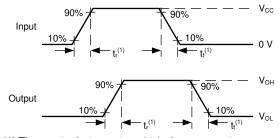


(1) C_L includes probe and test-fixture capacitance.

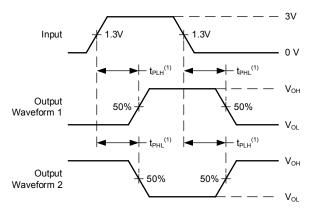




 (1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.
 Figure 6-2. Voltage Waveforms, Propagation Delays for Standard CMOS Inputs



 (1) The greater between t_r and t_f is the same as t_t.
 Figure 6-3. Voltage Waveforms, Input and Output Transition Times for Standard CMOS Inputs



(1) The greater between t_{PLH} and t_{PHL} is the same as $t_{\mathsf{pd}}.$





7 Detailed Description

7.1 Overview

The CD74HC93 and CD74HCT93 are high-speed silicon-gate CMOS devices and are pin-compatible with low power Schottky TTL (LSTTL). These 4-bit binary ripple counters consist of four flip-flops internally connected to provide a divide-by-two section and a divide-by-eight section. Each section has a separate clock input ($\overline{CP0}$ and $\overline{CP1}$) to initiate state changes of the counter on the HIGH to LOW clock transition. State changes of the Q_n outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used for clocks or strobes.

A gated AND asynchronous reset (MR1 and MR2) is provided which overrides both clocks and resets (clears) all flip-flops.

Because the output from the divide-by-two section is not internally connected to the succeeding stages, the device may be operated in various counting modes.

In a 4-bit ripple counter the output Q0 must be connected externally to input $\overline{CP1}$. The input count pulses are applied to clock input $\overline{CP0}$. Simultaneous frequency divisions of 2, 4, 8, and 16 are performed at the Q₀, Q₁, Q₂, and Q₃ outputs as shown in the function table. As a 3-bit ripple counter the input count pulses are applied to input $\overline{CP1}$.

Simultaneous frequency divisions of 2, 4, and 8 are available at the Q_1 , Q_2 , Q_3 outputs. Independent use of the first flipflop is available if the reset function coincides with the reset of the 3-bit ripple-through counter.

7.2 Functional Block Diagram

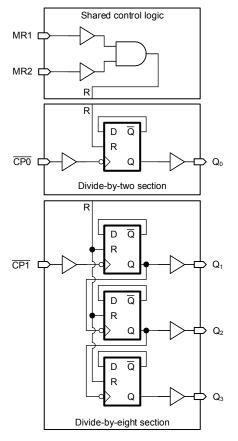


Figure 7-1. Functional Block Diagram



7.3 Device Functional Modes

Truth Table								
COUNT		OUTP	UTS ⁽¹⁾					
COONT	Q ₀	Q 1	Q ₂	Q_3				
0	L	L	L	L				
1	Н	L	L	L				
2	L	Н	L	L				
3	Н	Н	L	L				
4	L	L	Н	L				
5	Н	L	Н	L				
6	L	Н	Н	L				
7	Н	Н	Н	L				
8	L	L	L	Н				
9	Н	L	L	Н				
10	L	Н	L	Н				
11	Н	Н	L	Н				
12	L	L	Н	Н				
13	Н	L	Н	Н				
14	L	Н	Н	Н				
15	Н	Н	Н	Н				

(1) H = High voltage level, L = Low voltage level.

Table 7-1. Mode Selection

RESET C	OUTPUTS		OUTPUTS ⁽¹⁾				
MR1	MR2	Q ₀	Q ₁	Q ₂	Q ₃		
Н	Н	L	L	L	L		
L	Н	Count	Count	Count	Count		
Н	L						
L	L						

(1) H = High voltage level, L = Low voltage level.



8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Documentation Support

10.1.1 Related Documentation

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package		Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material (6)	(3)		(4/5)	
CD74HC93E	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC93E	Samples
CD74HC93EE4	ACTIVE	PDIP	Ν	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC93E	Samples
CD74HC93M	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-55 to 125	HC93M	
CD74HC93M96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	HC93M	Samples
CD74HC93MT	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-55 to 125	HC93M	
CD74HCT93E	ACTIVE	PDIP	Ν	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT93E	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures. "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



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PACKAGE OPTION ADDENDUM

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

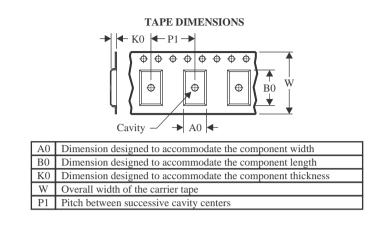
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All	dimensions are nominal												
	Device	0	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	CD74HC93M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
	CD74HC93M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



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PACKAGE MATERIALS INFORMATION

17-Mar-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CD74HC93M96	SOIC	D	14	2500	356.0	356.0	35.0	
CD74HC93M96	SOIC	D	14	2500	356.0	356.0	35.0	

TEXAS INSTRUMENTS

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17-Mar-2024

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HC93E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC93E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC93EE4	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC93EE4	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT93E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT93E	N	PDIP	14	25	506	13.97	11230	4.32

D0014A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



D0014A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0014A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



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